

EAST - [2456.wsp.1]

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BRS

ISNR:

Pending

00:11: (0) 63 and ('HCl' hydrogen adj chloride hydrochloric)

Active

L19: (1529) (plasma with ('HCl' hydrogen adj chloride hydrochloric))

L20: (737) plasma with (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-m...

L21: (16722) plasma with (ferromagnetic magnetic magnetic magneticresistive magnetization )

L27: (17) 26 and ('NiFe' 'CoFe' 'NiFeCo' 'Ru')

L51: (694) ('PtMn' 'IrMn')

L57: (366) 19 and (plasma adj etch\$3)

L58: (103) 57 and (ferromagnetic magnetic magnetic magneticresistive magnetization )

L59: (24) 57 and ((ferromagnetic magnetic magneticresistive magnetization ) with (layer film m...

L60: (1) 19 and 20

L61: (34) 19 and (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic )

L63: (316) 20 and 21

L64: (26) 63 and ('HCl' hydrogen adj chloride hydrochloric)

L66: (1) ("6491832").PN.

L67: (1) ("4439294").PN.

Failed

Plurals

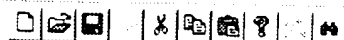
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63 and ('HCl' hydrogen adj chloride hydrochloric)

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L67: (1) ("4439294").PN.

L68: (26) 63 and ('HCl' hydrogen adj chloride hydrochloric)

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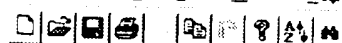


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2	<input type="checkbox"/>	<input type="checkbox"/>	US 6106895 A	20000822	9	Magnetic recording medium and process for producing the same	427/129	156/345.31;
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6077788 A	20000620	28	Method and apparatus for processing samples	438/706	427/387
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6036816 A	20000314	30	Apparatus for processing a sample having a metal laminate	156/345.22	438/710
5	<input type="checkbox"/>	<input type="checkbox"/>	US 5976257 A	19991102	60	Apparatus for continuously forming a large area deposited film by means of	118/718	134/1.3;
6	<input type="checkbox"/>	<input type="checkbox"/>	US 5952245 A	19990914	28	Method for processing samples	438/720	156/345.31
7	<input type="checkbox"/>	<input type="checkbox"/>	US 5922454 A	19990713	17	Magnetic recording medium	428/328	118/723MA;
8	<input type="checkbox"/>	<input type="checkbox"/>	US 5908683 A	19990601	21	Magnetic recording medium	428/141	118/729;
9	<input type="checkbox"/>	<input type="checkbox"/>	US 5888338 A	19990330	38	Magnetron plasma processing apparatus and processing method	156/345.46	134/1.2;
10	<input type="checkbox"/>	<input type="checkbox"/>	US 5876833 A	19990302	16	Magnetic recording medium containing magnetic powder and a po	428/141	438/718
11	<input type="checkbox"/>	<input type="checkbox"/>	US 5868854 A	19990209	32	Method and apparatus for processing samples	134/1.3	428/329;
12	<input type="checkbox"/>	<input type="checkbox"/>	US 5848684 A	19981215	8	Method for transporting magnetic	198/805	428/328;

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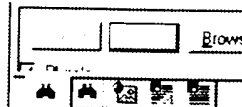
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✓ L67: (1) ("4439294").PN.

✓ L68: (26) 63 and ('HCl' hydrogen adj chloride hydrochloric)

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	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
13	<input type="checkbox"/>	<input type="checkbox"/>	US 5718964 A	19980217	23	Magnetic recording medium	428/141	428/323;
14	<input type="checkbox"/>	<input type="checkbox"/>	US 5637393 A	19970610	15	Magnetic recording medium and its manufacturing method	428/332	428/328;
15	<input type="checkbox"/>	<input type="checkbox"/>	US 5540957 A	19960730	14	Method of manufacturing a magnetic recording medium	427/535	428/336;
16	<input type="checkbox"/>	<input type="checkbox"/>	US 5496607 A	19960305	23	Magnetic recording medium	428/65.3	428/408;
17	<input type="checkbox"/>	<input type="checkbox"/>	US 5352501 A	19941004	36	Longitudinal magnetic recording medium comprising a circumferential	428/65.7	427/131;
18	<input type="checkbox"/>	<input type="checkbox"/>	US 5320707 A	19940614	36	Dry etching method	216/69	427/576;
19	<input type="checkbox"/>	<input type="checkbox"/>	US 5080971 A	19920114	23	Magnetic recording medium	428/336	428/336;
20	<input type="checkbox"/>	<input type="checkbox"/>	US 5069967 A	19911203	23	Magnetic recording medium	428/336	428/694B;
21	<input type="checkbox"/>	<input type="checkbox"/>	US 5057623 A	19911015	18	Organic fluorine compound	564/82	428/336;
22	<input type="checkbox"/>	<input type="checkbox"/>	US 4971880 A	19901120	14	Developer containing halogenated amorphous carbon particles prepared	430/111.34	428/409;
23	<input type="checkbox"/>	<input type="checkbox"/>	US 4966648 A	19901030	10	Process for producing thin film magnetic head	216/22	216/77;
24	<input type="checkbox"/>	<input type="checkbox"/>	US 4911812 A	19900327	8	Plasma treating method and apparatus	204/192.32	438/720

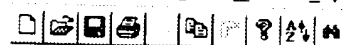
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LS9: (24) 57 and ((ferromagnetic magnetic magnetoresistive magnetization) with (layer film m...

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✓ L57: (366) 19 and (plasma adj etch\$3)

✓ L58: (103) 57 and (ferromagnetic magnetic magnetic magneticresistive magnetization )

✓ L59: (24) 57 and ((ferromagnetic magnetic magneticresistive magnetization ) with (layer film m...



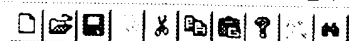
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14	<input type="checkbox"/>	<input type="checkbox"/>	US 5368684 A	19941129	9	Etching method for a	438/719	216/41;
15	<input type="checkbox"/>	<input type="checkbox"/>	US 5202061 A	19930413	17	silicon-containing layer using hydroge	252/500	438/711;
16	<input type="checkbox"/>	<input type="checkbox"/>	US 5200112 A	19930406	19	Electrically conductive polymeric	252/500	438/732
17	<input type="checkbox"/>	<input type="checkbox"/>	US 5198153 A	19930330	19	materials and uses thereof	252/500	427/372.2;
18	<input type="checkbox"/>	<input type="checkbox"/>	US 5190637 A	19930302	20	Electrically conductive polymeric	252/500	427/384;
19	<input type="checkbox"/>	<input type="checkbox"/>	US 4996077 A	19910226	22	materials and uses thereof	252/500	428/500;
20	<input type="checkbox"/>	<input type="checkbox"/>	US 4823177 A	19890418	8	Electrically conductive polymeric	252/500	428/688;
21	<input type="checkbox"/>	<input type="checkbox"/>	US 4668338 A	19870526	10	Formation of microstructures by	205/118	205/125
22	<input type="checkbox"/>	<input type="checkbox"/>	US 4439294 A	19840327	6	multiple level deep X-ray lithography	204/192.35	118/719;
23	<input type="checkbox"/>	<input type="checkbox"/>	EP 535540 A	19930407	5	Distributed ECR remote plasma	204/192.35	118/722;
24	<input checked="" type="checkbox"/>	<input type="checkbox"/>	EP 407169 A	19910109		processing and apparatus	204/192.35	257/424
						Method and device for magnetizing	204/192.35	204/298.37;
						thin films by the use of injected spin	204/192.35	204/192.37;
						Magnetron-enhanced plasma etching	204/192.35	216/22;
						process	204/192.35	
						Reactive ion etching of soft-magnetic	204/192.35	
						substrates	204/192.35	
						Plasma etching of aluminium@-contg.	204/192.35	
						layer - by using plasma formed from	204/192.35	
						Electron cyclotron resonance plasma	204/192.35	

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- ☒ L25: (682) 23 and (substrate wafer workpiece work adj piece)
- ☒ L26: (472) 25 and (plasma with etch\$3)
- ☒ L28: (112) 26 and (barrier)
- ☒ L29: (0) 26 and (electron adj barrier)
- ☒ L27: (17) 26 and ('NiFe' 'CoFe' 'NiFeCo' 'Ru')
- ☒ L30: (9) 27 and magnetic

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DBs: USPAT; US-PGPUB; EPO; JPO; DEI ☒ Plurals

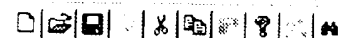
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1	<input type="checkbox"/>	<input type="checkbox"/>	US 20030013314 A1	20030116	18	Method of reducing particulates in a plasma etch chamber during a metal e	438/710		
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20020129900 A1	20020919	16	Method for processing specimens, an apparatus therefor and a method of m	156/345.31	156/345.32	
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20020037647 A1	20020328	55	Method of etching an anisotropic profile in platinum	438/689		
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6491832 B2	20021210	15	Method for processing specimens	216/22	216/67;	
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6323132 B1	20011127	52	Etching methods for anisotropic platinum profile	438/706	216/75;	
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6265318 B1	20010724	47	Iridium etchant methods for anisotropic profile	438/720	438/710;	
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6069035 A	20000530	12	Techniques for etching a transition metal-containing layer	438/220	438/720	
8	<input type="checkbox"/>	<input type="checkbox"/>	US 5892706 A	19990406	43	Fram, fram card, and card system using the same	365/145	365/226;	
9	<input type="checkbox"/>	<input type="checkbox"/>	US 5798964 A	19980825	43	FRAM, FRAM card, and card system using the same	365/145	365/65	
								365/149;	
								365/226;	




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L29: (0) 26 and (electron adj barrier)

L27: (17) 26 and ('NiFe' 'CoFe' 'NiFeCo' 'Ru')

L20: (0) 27 and magnetic

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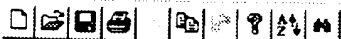
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1	<input type="checkbox"/>	<input type="checkbox"/>	US 20030037802 A1	20030227	18	Semiconductor treating apparatus and cleaning method of the same	134/1.1	118/715; 156/345.33
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20030013314 A1	20030116	18	Method of reducing particulates in a plasma etch chamber during a metal e	438/710	
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20020190024 A1	20021219	31	Etching method and cleaning method of chemical vapor growth apparatus	216/37	118/715; 118/724;
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20020129900 A1	20020919	16	Method for processing specimens, an apparatus therefor and a method of m	156/345.31	156/345.32
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20020037647 A1	20020328	55	Method of etching an anisotropic profile in platinum	438/689	
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6518106 B2	20030211	7	Semiconductor device and a method therefor	438/157	257/250; 257/331;
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6495054 B1	20021217	28	Etching method and cleaning method of chemical vapor growth apparatus	216/58	134/1.1; 216/63;
8	<input type="checkbox"/>	<input type="checkbox"/>	US 6491832 B2	20021210	15	Method for processing specimens	216/22	216/67; 216/75;
9	<input type="checkbox"/>	<input type="checkbox"/>	US 6410991 B1	20020625	31	Semiconductor device and method of manufacturing the same	257/392	257/607; 438/423;
10	<input type="checkbox"/>	<input type="checkbox"/>	US 6323132 B1	20011127	52	Etching methods for anisotropic platinum profile	438/706	438/710; 438/720
11	<input type="checkbox"/>	<input type="checkbox"/>	US 6265318 B1	20010724	47	Iridium etchant methods for anisotropic profile	438/720	216/67; 216/75;
12	<input type="checkbox"/>	<input type="checkbox"/>	US 6261967 B1	20010717	11	Easy to remove hard mask layer for semiconductor device fabrication	438/717	438/240; 438/393;

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☒ L29: (0) 26 and (electron adj barrier)

☒ L27: (17) 26 and ('NiFe' 'CoFe' 'NiFeCo' 'Ru')

☒ L20: (0) 27 and magnetic

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6	<input type="checkbox"/>	<input type="checkbox"/>	US 6518106 B2	20030211	7	Semiconductor device and a method therefor	438/157	257/250;	
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6495054 B1	20021217	28	Etching method and cleaning method of chemical vapor growth apparatus	216/58	257/331;	
8	<input type="checkbox"/>	<input type="checkbox"/>	US 6491832 B2	20021210	15	Method for processing specimens	216/22	134/1.1;	
9	<input type="checkbox"/>	<input type="checkbox"/>	US 6410991 B1	20020625	31	Semiconductor device and method of manufacturing the same		216/63;	
10	<input type="checkbox"/>	<input type="checkbox"/>	US 6323132 B1	20011127	52	Etching methods for anisotropic platinum profile	438/706	216/67;	
11	<input type="checkbox"/>	<input type="checkbox"/>	US 6265318 B1	20010724	47	Iridium etchant methods for anisotropic profile	438/720	216/75;	
12	<input type="checkbox"/>	<input type="checkbox"/>	US 6261967 B1	20010717	11	Easy to remove hard mask layer for semiconductor device fabrication	438/717	257/607;	
13	<input type="checkbox"/>	<input type="checkbox"/>	US 6069035 A	20000530	12	Techniques for etching a transition metal-containing layer	438/220	438/423;	
14	<input type="checkbox"/>	<input type="checkbox"/>	US 5892706 A	19990406	43	Fram, fram card, and card system using the same	365/145	438/710;	
15	<input type="checkbox"/>	<input type="checkbox"/>	US 5798964 A	19980825	43	FRAM, FRAM card, and card system using the same	365/145	438/720	
16	<input type="checkbox"/>	<input type="checkbox"/>	US 5496437 A	19960305	13	Reactive ion etching of lead zirconate titanate and ruthenium oxide thin films	438/3	365/226;	
17	<input type="checkbox"/>	<input type="checkbox"/>	US 6306312 B	20020710	10	Anisotropically etching a gold layer through an aperture in hardmask invol		216/6;	
								216/76;	

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1. Number	Hits	Search Text	DB	Time stamp
1	264825	magnetic near3 (layer film material memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:34
2	5642	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:28
3	16	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (plasma with 'HCl')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:47
4	873	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (chloride chloride-containing))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:48
5	873	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (chloride chloride-containing)) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:49
6	8	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (chloride chloride-containing)) and plasma and (plasma with ('HCl' hydrogen adj chloride hydrochloric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:51
7	282	(plasma with ('HCl' hydrogen adj chloride hydrochloric)) and magnetic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:08
8	0	(plasma with ('HCl' hydrogen adj chloride hydrochloric)) and (anti adj magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:52
9	0	(plasma with ('HCl' hydrogen adj chloride hydrochloric)) and (anti-magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:51
10	0	plasma with (anti-magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:00
11	1	plasma with ('PtMn' 'IrMn')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:54
12	3	plasma with (antimagnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:01

Number	Hits	Search Text	DB	Time stamp
1	264825	magnetic near3 (layer film material memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:34
2	5642	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:28
3	16	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (plasma with 'HCl')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:47
4	873	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (chloride chloride-containing))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:48
5	873	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (chloride chloride-containing)) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:49
6	8	((((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (chloride chloride-containing)) and plasma) and (plasma with ('HCl' hydrogen adj chloride hydrochloric)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:51
7	282	(plasma with ('HCl' hydrogen adj chloride hydrochloric)) and magnetic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:08
8	0	(plasma with ('HCl' hydrogen adj chloride hydrochloric)) and (anti adj magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:52
9	0	(plasma with ('HCl' hydrogen adj chloride hydrochloric)) and (anti-magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:53
10	0	plasma with (anti-magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:00
11	1	plasma with ('PtMn' 'IrMn')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:54
12	3	plasma with (antimagnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:01

13	724	plasma with (nonmagnetic non-magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:02
16	191	plasma with (magnetoresistive magnetization)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:06
17	14	plasma with (nonferromagnetic antiferromagnetic non-ferromagnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:16
18	737	(( plasma with (nonmagnetic non-magnetic)) or ( plasma with (nonferromagnetic antiferromagnetic non-ferromagnetic))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:06
19	1529	(plasma with ('HCl' hydrogen adj chloride hydrochloric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:08
20	737	plasma with (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:17
21	16722	plasma with (ferromagnetic magnetic magnetic magneticresistive magnetization )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:19
22	943	(( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (plasma with (etch\$3 reactor chamber source material gas\$2)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:30
23	943	(( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (plasma with (etch\$3 reactor chamber source material gas\$2))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:31
25	682	(( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (plasma with (etch\$3 reactor chamber source material gas\$2)))) and (substrate wafer workpiece work adj piece)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:32

13	724	plasma with (nonmagnetic non-magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:02
16	191	plasma with (magnetoresistive magnetization)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:06
17	14	plasma with (nonferromagnetic antiferromagnetic non-ferromagnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:16
18	737	( plasma with (nonmagnetic non-magnetic)) or ( plasma with (nonferromagnetic antiferromagnetic non-ferromagnetic))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:06
19	1529	(plasma with ('HCl' hydrogen adj chloride hydrochloric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:58
20	737	plasma with (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:49
21	16722	plasma with (ferromagnetic magnetic magnetic magneticresistive magnetization )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:19
22	943	(( plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (plasma with (etch\$3 reactor chamber source material gas\$2))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:30
23	943	(( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (( plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (plasma with (etch\$3 reactor chamber source material gas\$2)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:31
25	682	(( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (( plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (plasma with (etch\$3 reactor chamber source material gas\$2)))) and (substrate wafer workpiece work adj piece)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:39
26	472	(( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (( plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (plasma with (etch\$3 reactor chamber source material gas\$2)))) and (substrate wafer workpiece work adj piece)) and (plasma with etch\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:43
28	112	(( (( plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (( plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (plasma with (etch\$3 reactor chamber source material gas\$2)))) and (substrate wafer workpiece work adj piece)) and (plasma with etch\$3)) and (barrier)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:45

27	17	(( (plasma with ('HCl' hydrogen adj chloride hydrochloric) ) and ((plasma with ('HCl' hydrogen adj chloride hydrochloric) ) and (plasma with (etch\$3 reactor chamber source material gas\$2))) and (substrate wafer workpiece work adj piece)) and (plasma with etch\$3)) and ('NiFe' 'CoFe' 'NiFeCo' 'Ru'))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:03
30	9	(( (( (plasma with ('HCl' hydrogen adj chloride hydrochloric) ) and ((plasma with ('HCl' hydrogen adj chloride hydrochloric) ) and (plasma with (etch\$3 reactor chamber source material gas\$2))) and (substrate wafer workpiece work adj piece)) and (plasma with etch\$3)) and ('NiFe' 'CoFe' 'NiFeCo' 'Ru')) and magnetic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:47
36	1	(( (plasma with ('HCl' hydrogen adj chloride hydrochloric) ) and ((plasma with (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:04
37	1	(( (plasma with ('HCl' hydrogen adj chloride hydrochloric) ) and ((plasma with (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:08
38	738	plasma with (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:52
39	1	(( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and ((plasma with (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:50
40	1	(( (plasma with (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic ) with ('HCl' hydrogen adj chloride hydrochloric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:53
41	1	(( (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic) with (('HCl' hydrogen adj chloride hydrochloric) with plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:55
42	1	(( (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic) with (('HCl' hydrogen adj chloride hydrochloric) with plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:56
43	738	(( (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic) with plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:56
44	1529	(( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (plasma with ('HCl' hydrogen adj chloride hydrochloric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:59
45	1	(( (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic) with plasma ) and (plasma with ('HCl' hydrogen adj chloride hydrochloric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:59

Number	Hits	Search Text	DB	Time stamp
1	264825	magnetic near3 (layer film material memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:34
2	5642	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:28
3	16	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (plasma with 'HCl')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:47
4	873	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (chloride chloride-containing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:48
5	873	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (chloride chloride-containing)) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:49
6	8	((magnetic near3 (layer film material memory)) and (plasma with (etch\$3 reactor chamber source material))) and (chloride chloride-containing)) and plasma and (plasma with ('HCl' hydrogen adj chloride hydrochloric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:51
7	282	(plasma with ('HCl' hydrogen adj chloride hydrochloric)) and magnetic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:08
8	0	(plasma with ('HCl' hydrogen adj chloride hydrochloric)) and (anti adj magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:52
9	0	(plasma with ('HCl' hydrogen adj chloride hydrochloric)) and (anti-magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:51
10	0	plasma with (anti-magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:00
11	1	plasma with ('PtMn' 'IrMn')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 08:54
12	3	plasma with (antimagnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:01

13	724	plasma with (nonmagnetic non-magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:02
16	191	plasma with (magnetoresistive magnetization)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:06
17	14	plasma with (nonferromagnetic antiferromagnetic non-ferromagnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:16
18	737	(( plasma with (nonmagnetic non-magnetic)) or ( plasma with (nonferromagnetic antiferromagnetic non-ferromagnetic)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:06
19	1529	(plasma with ('HCl' hydrogen adj chloride hydrochloric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:58
20	737	plasma with (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:49
21	16722	plasma with (ferromagnetic magnetic magnetic magnetoresistive magnetization )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:19
22	943	(( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (plasma with (etch\$3 reactor chamber source material gas\$2)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:30
23	943	(( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (plasma with (etch\$3 reactor chamber source material gas\$2))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:31
25	682	(( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (plasma with (etch\$3 reactor chamber source material gas\$2)))) and (substrate wafer workpiece work adj piece)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:39
26	472	(( (( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (plasma with (etch\$3 reactor chamber source material gas\$2)))) and (substrate wafer workpiece work adj piece)) and (plasma with etch\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:43
28	112	(( (( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (plasma with (etch\$3 reactor chamber source material gas\$2)))) and (substrate wafer workpiece work adj piece)) and (plasma with etch\$3)) and (barrier)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:45



27	17	(( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and ((plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (plasma with (etch\$3 reactor chamber source material gas\$2))) and (substrate wafer workpiece work adj piece)) and (plasma with etch\$3)) and ('NiFe' 'CoFe' 'NiFeCo' 'Ru')	USPAT. US-PGPUB. EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:30
30	9	(( (( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and ((plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (plasma with (etch\$3 reactor chamber source material gas\$2))) and (substrate wafer workpiece work adj piece)) and (plasma with etch\$3)) and ('NiFe' 'CoFe' 'NiFeCo' 'Ru')) and magnetic	USPAT. US-PGPUB. EPO; JPO; DERWENT; IBM_TDB	2003/03/17 09:47
36	1	(( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (plasma with (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic ))	USPAT. US-PGPUB. EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:04
37	1	(( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (plasma with (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic ))	USPAT. US-PGPUB. EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:08
38	738	plasma with (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic )	USPAT. US-PGPUB. EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:52
39	1	(( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (plasma with (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic ))	USPAT. US-PGPUB. EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:50
40	1	(( plasma with (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic )) with ('HCl' hydrogen adj chloride hydrochloric)	USPAT. US-PGPUB. EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:53
41	1	(( nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic) with (('HCl' hydrogen adj chloride hydrochloric) with plasma)	USPAT. US-PGPUB. EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:55
42	1	(( nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic) with (('HCl' hydrogen adj chloride hydrochloric) with plasma)	USPAT. US-PGPUB. EPO; JPO; DERWENT; IBM_TDB	2003/03/17 11:56
43	738	(( nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic) with plasma	USPAT. US-PGPUB. EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:13
44	1529	(( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (plasma with ('HCl' hydrogen adj chloride hydrochloric))	USPAT. US-PGPUB. EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:00
45	1	(( (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic) with plasma ) and (plasma with ('HCl' hydrogen adj chloride hydrochloric))	USPAT. US-PGPUB. EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:00

46	1	(( (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic) with plasma ) and ((plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (plasma with ('HCl' hydrogen adj chloride hydrochloric)) )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:00
47	1529	(plasma with ('HCl' hydrogen adj chloride hydrochloric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:34
49	34	(( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:32
50	0	(( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and ('PtMn' 'IrMn'))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:24
51	694	('PtMn' 'IrMn')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:25
52	1	('PtMn' 'IrMn') with plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:25
53	45	(( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and ('NiFe' 'CoFe' 'NiFeCo' 'Ru'))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:30
54	34	(( (plasma with ('HCl' hydrogen adj chloride hydrochloric)) ) and (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic antimagnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:33
55	4427	plasma and (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic antimagnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:33
56	34	(plasma and (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic anti-ferromagnetic anti-magnetic antimagnetic) ) and (plasma with ('HCl' hydrogen adj chloride hydrochloric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 12:46